

High voltage power Schottky rectifier

Main product characteristics

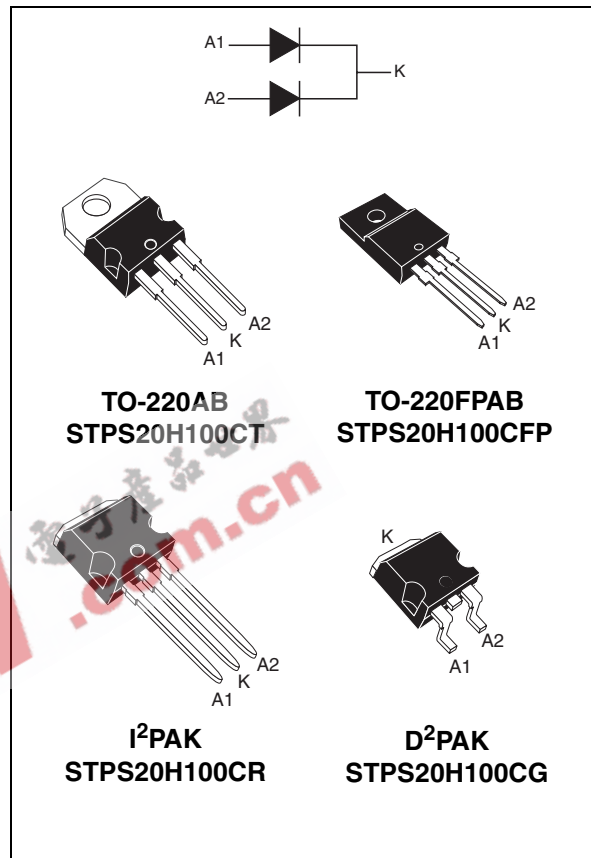
$I_{F(AV)}$	2 x 10 A
V_{RRM}	100 V
T_j (max)	175° C
V_F (max)	0.64 V

Features and benefits

- Negligible switching losses
- High junction temperature capability
- Good trade off between leakage current and forward voltage drop
- Low leakage current
- Avalanche rated
- Insulated package: TO-220FPAB
Insulating voltage = 2000 V DC
Capacitance = 45 pF
- Avalanche capability specified

Description

Dual center tap schottky rectifier designed for high frequency miniature switched mode power supplies such as adaptators and on board DC/DC converters.



1 Characteristics

Table 1. Absolute ratings (limiting values, per diode)

Symbol	Parameter			Value	Unit	
V_{RRM}	Repetitive peak reverse voltage			100	V	
$I_{F(RMS)}$	RMS forward current			30	A	
$I_{F(AV)}$	Average forward current $\delta = 0.5$	TO-220AB D ² PAK / I ² PAK	$T_c = 160^\circ\text{C}$	Per diode	10	A
		TO-220FPAB	$T_c = 145^\circ\text{C}$	Per device	20	
I_{FSM}	Surge non repetitive forward current		$t_p = 10\text{ ms}$ sinusoidal		250	A
I_{RRM}	Repetitive peak reverse current		$t_p = 2\ \mu\text{s}$ square F= 1 kHz		1	A
I_{RSM}	Non repetitive peak reverse current		$t_p = 100\ \mu\text{s}$ square		3	A
P_{ARM}	Repetitive peak avalanche power		$t_p = 1\ \mu\text{s}$ $T_j = 25^\circ\text{C}$		10800	W
T_{stg}	Storage temperature range			-65 to + 175	$^\circ\text{C}$	
T_j	Maximum operating junction temperature ⁽¹⁾			175	$^\circ\text{C}$	
dV/dt	Critical rate of rise of reverse voltage			10000	V/ μs	

1. $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$ condition to avoid thermal runaway for a diode on its own heatsink

Table 2. Thermal resistance

Symbol	Parameter			Value	Unit
$R_{th(j-c)}$	Junction to case	TO-220AB / D ² PAK / I ² PAK	Per diode	1.6	$^\circ\text{C/W}$
		TO-220FPAB	Per diode	4	
		TO-220AB / D ² PAK / I ² PAK	Total	0.9	$^\circ\text{C/W}$
		TO-220FPAB	Total	3.2	
$R_{th(c)}$		TO-220AB / D ² PAK / I ² PAK	Coupling	0.15	$^\circ\text{C/W}$
		TO-220FPAB	Coupling	2.5	

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_j(\text{diode 1}) = P(\text{diode1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

Table 3. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			4.5	μA
		$T_j = 125^\circ\text{C}$			2	6	mA
$V_F^{(2)}$	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 8\text{ A}$			0.71	V
		$T_j = 25^\circ\text{C}$	$I_F = 10\text{ A}$			0.77	
		$T_j = 25^\circ\text{C}$	$I_F = 16\text{ A}$			0.81	
		$T_j = 25^\circ\text{C}$	$I_F = 20\text{ A}$			0.88	
		$T_j = 125^\circ\text{C}$	$I_F = 8\text{ A}$		0.56	0.58	
		$T_j = 125^\circ\text{C}$	$I_F = 10\text{ A}$		0.59	0.64	
		$T_j = 125^\circ\text{C}$	$I_F = 16\text{ A}$		0.65	0.68	
		$T_j = 125^\circ\text{C}$	$I_F = 20\text{ A}$		0.67	0.73	

1. Pulse test: $t_p = 5\text{ ms}$, $\delta < 2\%$

2. Pulse test: $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 0.55 \times I_{F(AV)} + 0.009 I_{F(RMS)}^2$$

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Figure 1. Average forward power dissipation versus average forward current (per diode)

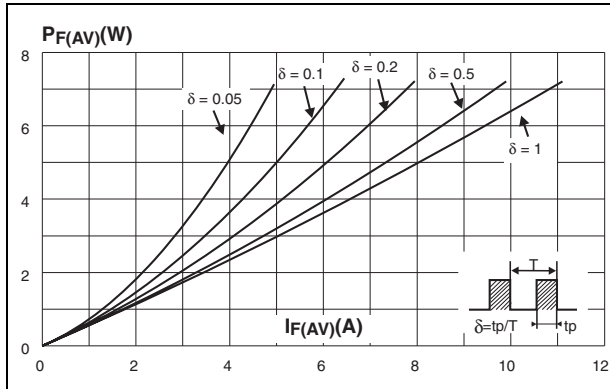


Figure 2. Average forward current versus ambient temperature ($\delta = 0.5$, per diode)

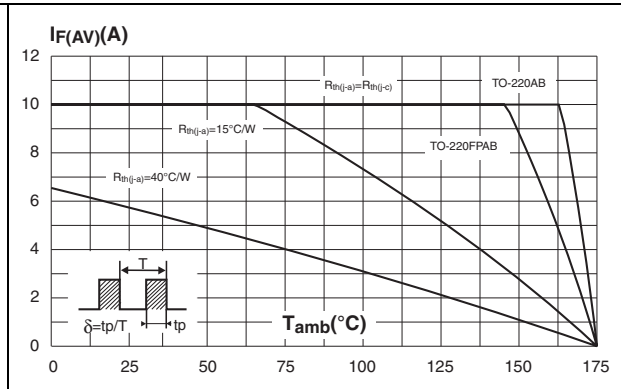


Figure 3. Normalized avalanche power derating versus pulse duration

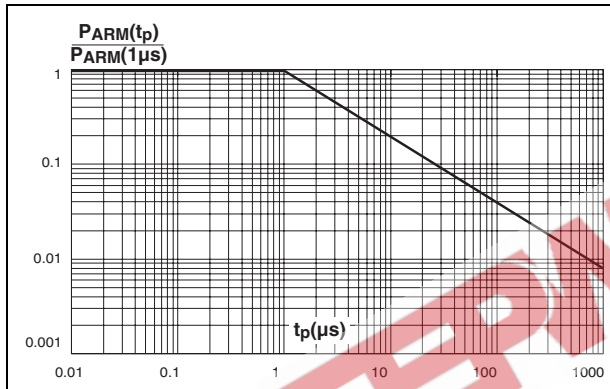


Figure 4. Normalized avalanche power derating versus junction temperature

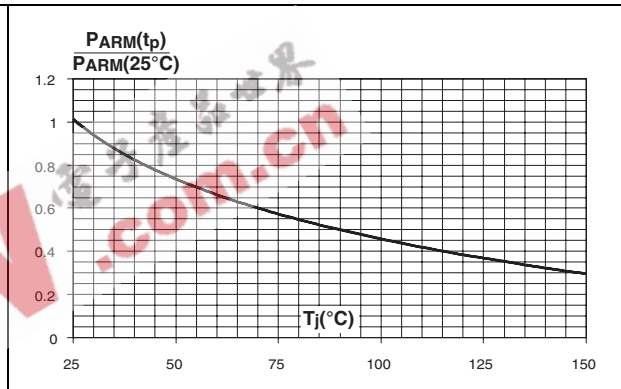


Figure 5. Non repetitive surge peak forward current versus overload duration (maximum values, per diode, TO-220AB, D²PAK, I²PAK)

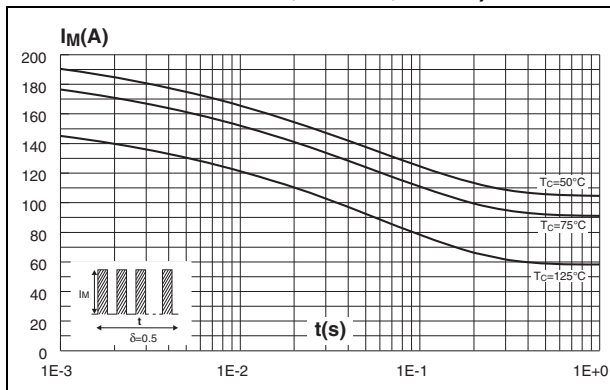


Figure 6. Non repetitive surge peak forward current versus overload duration (maximum values, per diode, TO-220FPAB)

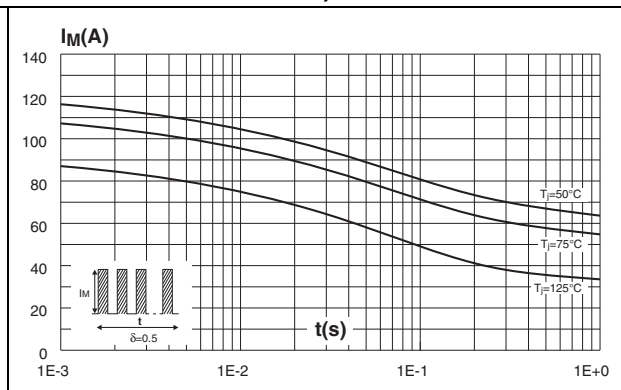


Figure 7. Relative variation of thermal impedance junction to case versus pulse duration (per diode, TO-220AB, D²PAK, I²PAK)

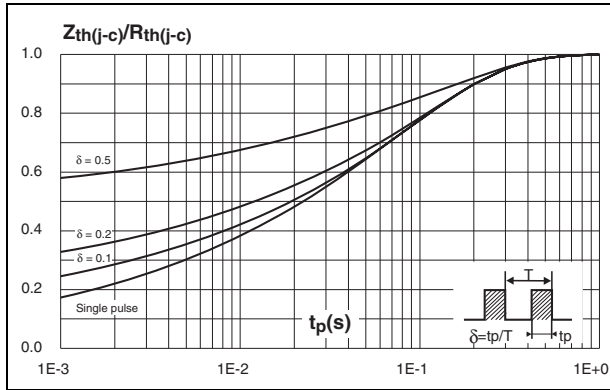


Figure 8. Relative variation of thermal impedance junction to case versus pulse duration (per diode, TO-220FPAB)

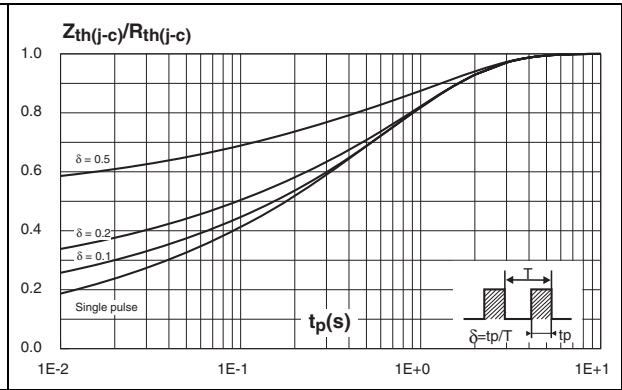


Figure 9. Reverse leakage current versus reverse voltage applied (typical values, per diode)

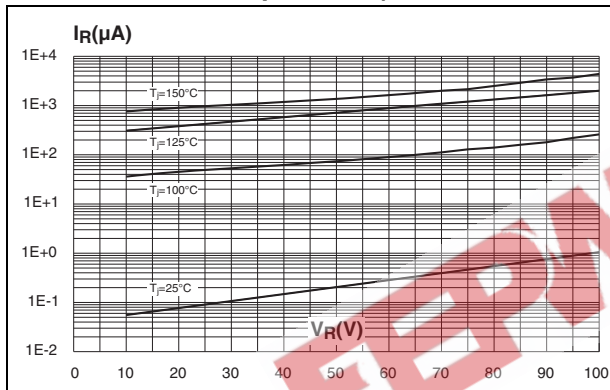


Figure 10. Junction capacitance versus reverse voltage applied (typical values, per diode)

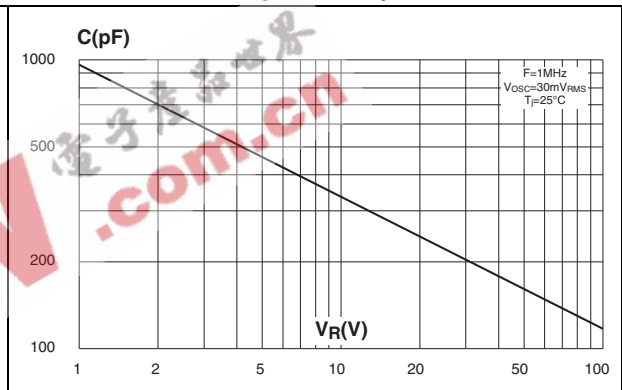


Figure 11. Forward voltage drop versus forward current (maximum values, per diode)

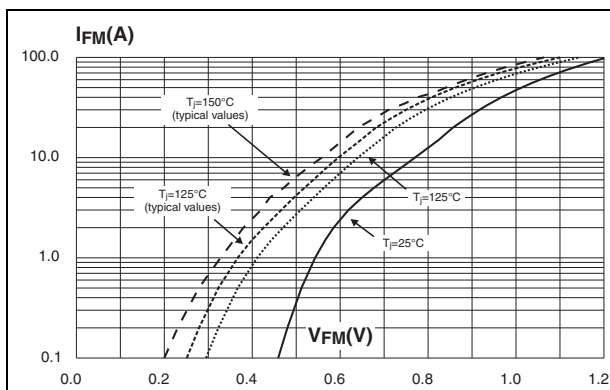
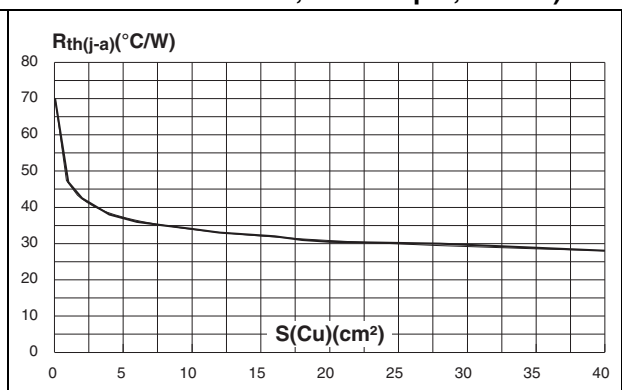


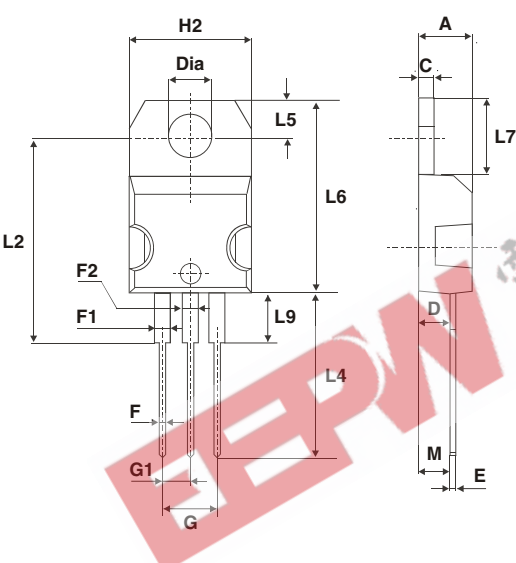
Figure 12. Thermal resistance junction to ambient versus copper surface under tab (epoxy printed circuit board FR4, Cu = 35 μm , D²PAK)



2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.55 Nm
- Maximum torque value: 0.70 Nm

Table 4. TO-220AB dimensions



Ref	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
C	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
E	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
F2	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
G1	2.40	2.70	0.094	0.106
H2	10	10.40	0.393	0.409
L2	16.4 typ.		0.645 typ.	
L4	13	14	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
M	2.6 typ.		0.102 typ.	
Diam.	3.75	3.85	0.147	0.151

Table 5. TO-220FPAB dimensions

Ref	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.4	4.6	0.173	0.181
B	2.5	2.7	0.098	0.106
D	2.5	2.75	0.098	0.108
E	0.45	0.70	0.018	0.027
F	0.75	1	0.30	0.039
F1	1.15	1.70	0.045	0.067
F2	1.15	1.70	0.045	0.067
G	4.95	5.20	0.195	0.205
G1	2.4	2.7	0.094	0.106
H	10	10.4	0.393	0.409
L2	16 typ.		0.63 typ.	
L3	28.6	30.6	1.126	1.205
L4	9.8	10.6	0.386	0.417
L5	2.9	3.6	0.114	0.142
L6	15.9	16.4	0.626	0.646
L7	9.00	9.30	0.354	0.366
Dia.	3	3.20	0.118	0.126

Table 6. D²PAK dimensions

Ref	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
A1	2.49	2.69	0.098	0.106
A2	0.03	0.23	0.001	0.009
B	0.70	0.93	0.027	0.037
B2	1.14	1.70	0.045	0.067
C	0.45	0.60	0.017	0.024
C2	1.23	1.36	0.048	0.054
D	8.95	9.35	0.352	0.368
E	10.00	10.40	0.393	0.409
G	4.88	5.28	0.192	0.208
L	15.00	15.85	0.590	0.624
L2	1.27	1.40	0.050	0.055
L3	1.40	1.75	0.055	0.069
M	2.40	3.20	0.094	0.126
R	0.40 typ.		0.016 typ.	
V2	0°	8°	0°	8°

Figure 13. Footprint (dimensions in millimeters)

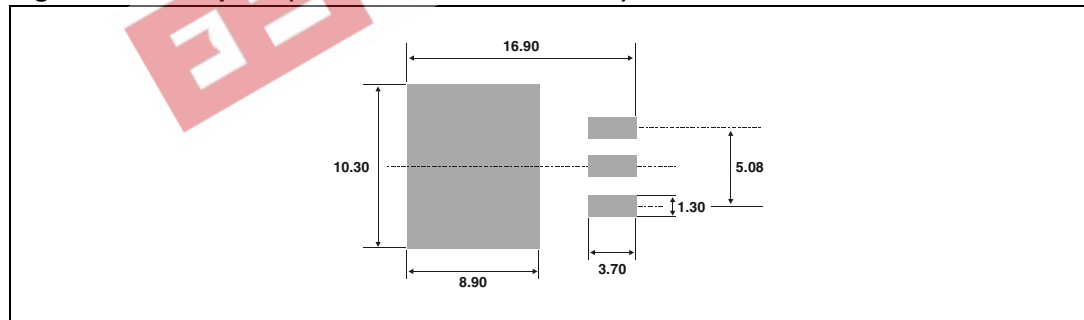


Table 7. I²PAK dimensions

Ref	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
A1	2.49	2.69	0.098	0.106
b	0.70	0.93	0.028	0.037
b1	1.14	1.17	0.044	0.046
b2	1.14	1.17	0.044	0.046
c	0.45	0.60	0.018	0.024
c2	1.23	1.36	0.048	0.054
D	8.95	9.35	0.352	0.368
e	2.40	2.70	0.094	0.106
E	10.0	10.4	0.394	0.409
L	13.1	13.6	0.516	0.535
L1	3.48	3.78	0.137	0.149
L2	1.27	1.40	0.050	0.055

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

3 Ordering information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS20H100CT	STPS20H100CT	TO-220AB	2.20 g	50	Tube
STPS20H100CFP	STPS20H100CFP	TO-220FPAB	2.0 g	50	Tube
STPS20H100CR	STPS20H100CR	I ² PAK	1.49 g	50	Tube
STPS20H100CG	STPS20H100CG	D ² PAK	1.48 g	50	Tube
STPS20H100CG-TR	STPS20H100CG	D ² PAK	1.48 g	1000	Tape & reel

4 Revision history

Date	Revision	Description of Changes
Jul-2003	4G	Last release.
21-Mar-2007	5	Removed ISOWATT package.

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